



P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	
- 20	0.0077 at V _{GS} = - 4.5 V	- 19	
	0.0094 at V _{GS} = - 2.5 V	- 17	
	0.0125 at V _{GS} = - 1.8 V	- 15	

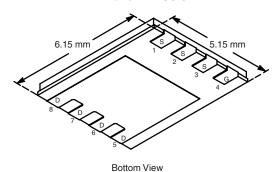
FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET[®] Power MOSFET
- New Low Thermal Resistance PowerPAK[®] Package with Low 1.07 mm Profile
- 100 % R_q Tested





PowerPAK SO-8

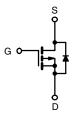


Ordering Information: Si7445DP-T1-E3 (Lead (Pb)-free)

Si7445DP-T1-GE3 (Lead (Pb)-free and Halogen-free)

APPLICATIONS

· Load Switch Battery Applications



P-Channel MOSFET

Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V_{DS}	- 20		V
Gate-Source Voltage		V_{GS}	± 8		
Continuous Drain Current (T = 150°C) ⁸	T _A = 25°C	I _D	- 19	- 12	٨
Continuous Drain Current (T _J = 150°C) ^a	T _A = 70°C		- 15	- 9	
Pulsed Drain Current		I _{DM}	- 50		Α
Continuous Source Current (Diode Conduction) ^a		I _S	- 4.3	- 1.6	
M	T _A = 25°C	P _D	5.4	1.9	W
Maximum Power Dissipation ^a	T _A = 70°C		3.4	1.2	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature)b, c			260		

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manianum lumption to Ameleianti	t ≤ 10 s	R _{thJA}	18	23	°C/W
Maximum Junction-to-Ambient ^a	Steady State		52	65	
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	1.0	1.3	

Notes

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See Solder Profile (<u>www.vishay.com/ppg?73257</u>). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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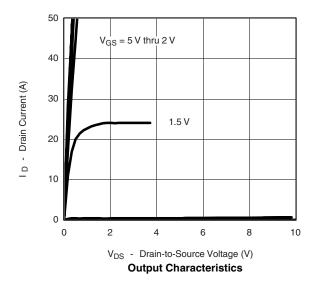


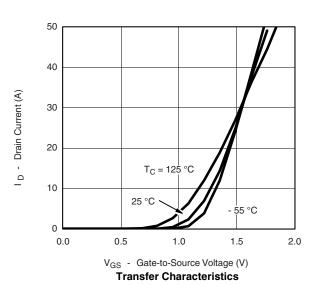
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit		
Static				•				
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.45		- 1.0	V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA		
Zero Gate Voltage Drain Current	I _{DSS} -	V _{DS} = - 20 V, V _{GS} = 0 V			- 1			
		V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 70 °C			- 10	μΑ		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 40			Α		
Drain-Source On-State Resistance ^a		V _{GS} = - 4.5 V, I _D = - 19 A		0.0064	0.0077			
	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 17 A		0.0078	0.0094	Ω		
		V _{GS} = - 1.8 V, I _D = - 10 A		0.0105	0.0125			
Forward Transconductance ^a g _{fs}		V _{DS} = - 15 V, I _D = - 19 A		75		S		
Diode Forward Voltage ^a	V_{SD}	I _S = - 4.3 A, V _{GS} = 0 V		- 0.65	- 1.1	V		
Dynamic ^b								
Total Gate Charge	Q_g			92	140			
Gate-Source Charge	Q _{gs} Q _{gd}	$V_{DS} = -15 \text{ V}, V_{GS} = -5 \text{ V}, I_{D} = -19 \text{ A}$		19		nC		
Gate-Drain Charge				16.5				
Gate Resistance	R_{g}		1	2	3.4	Ω		
Turn-On Delay Time	t _{d(on)}			40	60			
Rise Time	t _r	V_{DD} = - 15 V, R_L = 15 Ω		45	65	ns		
Turn-Off Delay Time		$I_D\cong$ - 1.0 A, V_{GEN} = - 4.5 V, R_g = 6 Ω		400	600			
Fall Time	t _f			190	290			
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 4.3 A, dI/dt = 100 A/μs		50	80			

Notes: a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

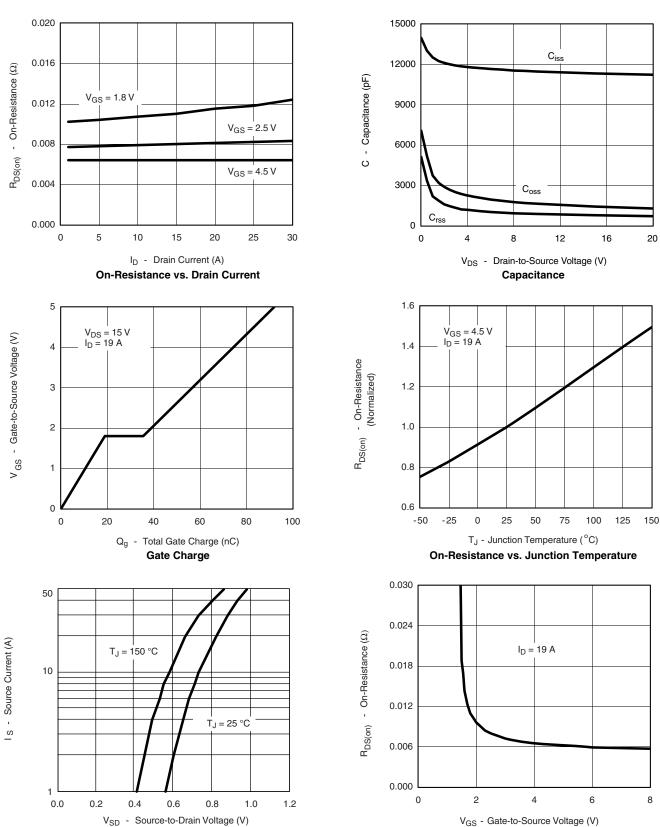








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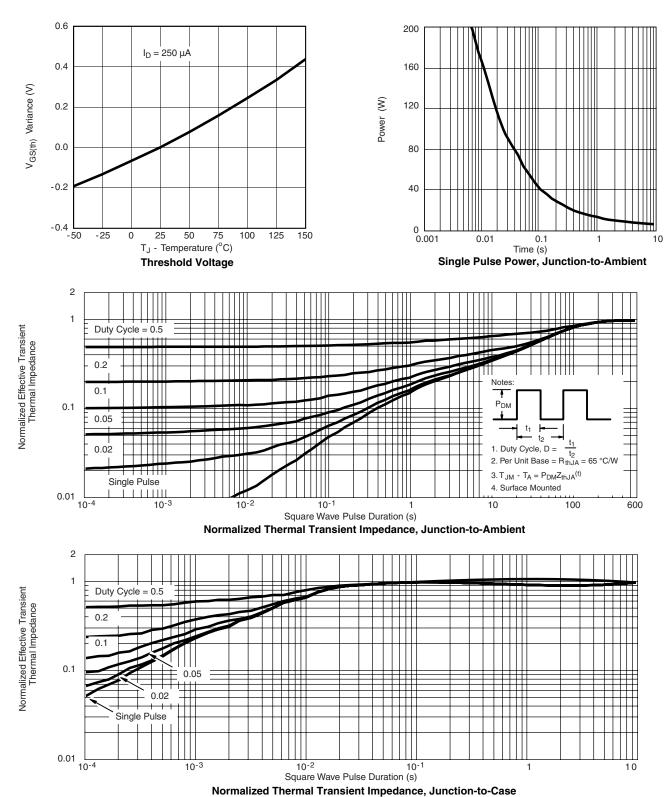
Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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